

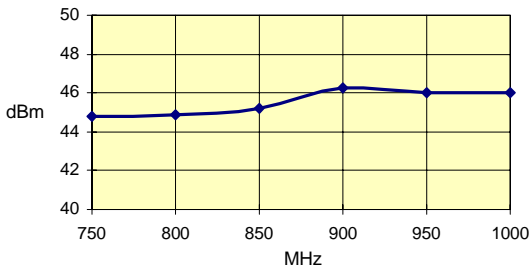
Product Description

Stanford Microdevices' SXL-208 amplifier is a high efficiency GaAs Heterojunction Bipolar Transistor (HBT) MMICs housed in low-cost surface-mountable plastic package. These HBT MMICs are fabricated using molecular beam epitaxial growth technology which produces reliable and consistent performance from wafer to wafer and lot to lot.

These amplifiers are specially designed for use as driver devices for infrastructure equipment in the 800-970 MHz cellular, ISM and narrowband PCS.

Its high linearity make it an ideal choice for multi-carrier as well as digital applications.

Output Third Order Intercept Point vs. Frequency



Electrical Specifications at Ta = 25C

Symbol	Parameters; Test Conditions: $Z_0 = 50 \text{ Ohms}$, $f = 800\text{-}970 \text{ MHz}$		Units	Min.	Typ.	Max.
P_{1dB}	Output Power at 1dB Compression	$f = 820\text{-}880 \text{ MHz}$ $f = 800\text{-}970 \text{ MHz}$	dBm dBm	30.0	30.5 30.0	
S_{21}	Power Gain	$f = 800\text{-}970 \text{ MHz}$	dB		18.0	
PAE	Power Added Efficiency	$f = 820\text{-}880 \text{ MHz}$ $f = 800\text{-}970 \text{ MHz}$	% %		44 40	
VSWR	Input VSWR	$f = 820\text{-}880 \text{ MHz}$ $f = 800\text{-}970 \text{ MHz}$	-		1.5:1 2.0:1	
VSWR	Output VSWR	$f = 820\text{-}880 \text{ MHz}$ $f = 800\text{-}970 \text{ MHz}$	-		1.5:1 2.5:1	
IP_3	Third Order Intercept Point	$f = 820\text{-}880 \text{ MHz}$ $f = 800\text{-}970 \text{ MHz}$	dBm dBm	43	46 45	
I_d	Device Current	$V_c = +5V$	mA		460	

SXL-208

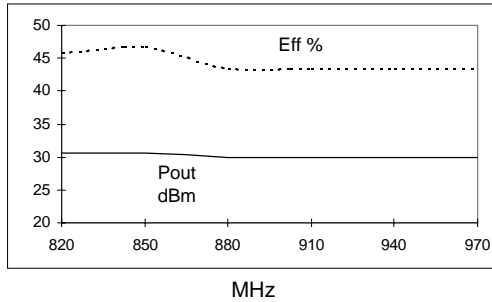
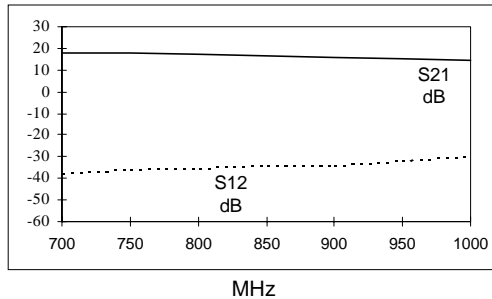
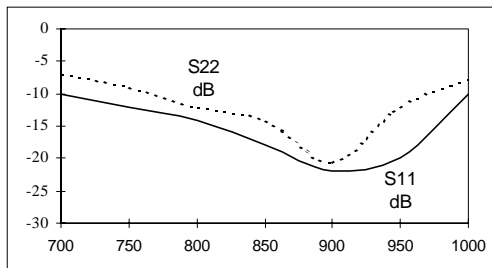
800-970 MHz 50 Ohm Power MMIC Amplifier

Product Features

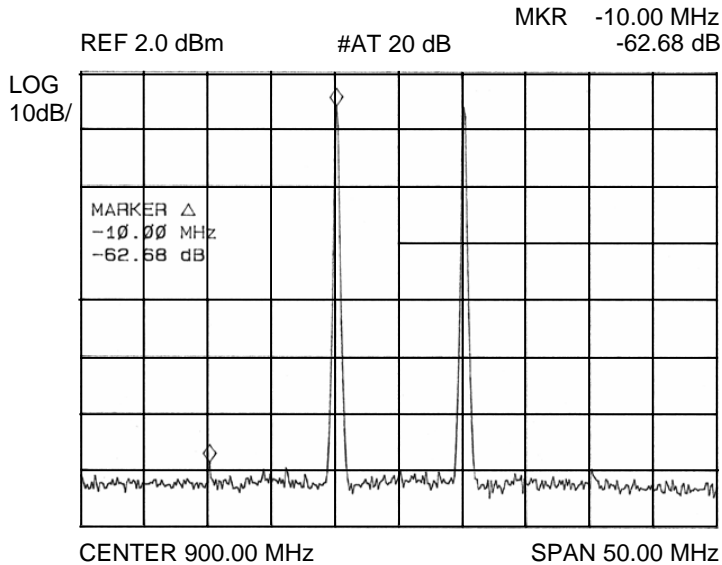
- Patented High Reliability GaAs HBT Technology
- High 3rd Order Intercept : +46dBm Typ. at 900 MHz
- High Gain : 18dB Typ. at 900 MHz
- Surface-Mountable Power Plastic Package

Applications

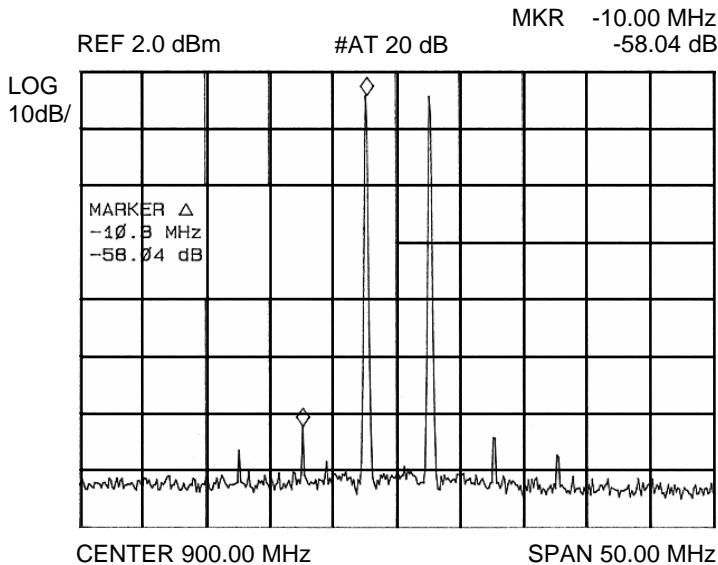
- Multi-Carrier Systems
- Basestation Applications

SXL-208 800-970 MHz Power MMIC Amplifier
Typical Performance at 25° C (Vc = 5.0V, Ic=460mA)
Output Power and Efficiency vs. Frequency

Gain and Isolation vs. Frequency

Input & Output Return Loss vs. Frequency


Third Order Intercept Point vs. Output Tone Power



Tone Power= +14dBm, IP3 = +46dBm



Tone Power= +17dBm, IP3 = +46dBm

Absolute Maximum Ratings

Parameter	Absolute Maximum
Device Voltage	7V
Device Current	700mA
Power Dissipation	5000mW
RF Input Power	100mW
Junction Temperature	+175C
Operating Temperature	-45C to +85C
Storage Temperature	-65C to +175C

Notes:

1. Operation of this device above any one of these parameters may cause permanent damage.

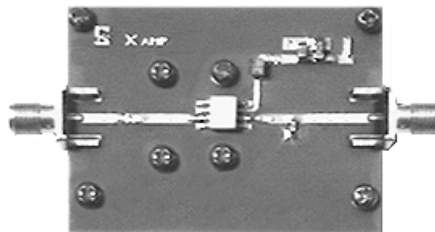
Part Number Ordering Information

Part Number	Devices Per Reel	Reel Size
SXL-208-TR1	500	7"
SXL-208-TR2	1000	13"
SXL-208-BLK	100/TRAY	-

**MTTF vs. Temperature
@ Id = 460mA**

Lead Temperature	Junction Temperature	MTTF (hrs)
+25C	+103C	>10,000,000
+60C	+138C	1,000,000
+85C	+163C	100,000

Thermal Resistance (Lead-Junction): 60° C/W



**SXL-208 Evaluation Board
(P/N SXL-208EB)**

**Application Schematic and Bias Circuit
for 900 MHz Operation**

